Haiyang

List of Publications by Year in descending order

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48 papers	1,333 citations	331670 21 h-index	361022 35 g-index
49 all docs	49 docs citations	49 times ranked	1991 citing authors

#	Article	IF	Citations
1	A review on sustainable synthetic approaches toward photoluminescent quantum dots. Green Chemistry, 2022, 24, 675-700.	9.0	26
2	Stable white emission and color-tunable electroluminescence achieved from n-ZnO/p-GaN nano-heterojunction decorated with CsPbBr3 and CsPbI3 quantum dots. Journal of Luminescence, 2022, 244, 118691.	3.1	5
3	Ultrafast growth of submillimeter-scale single-crystal MoSe2 by pre-alloying CVD. Nanoscale Horizons, 2022, , .	8.0	2
4	Directed exfoliating and ordered stacking of transition-metal-dichalcogenides. Nanoscale, 2022, 14, 7484-7492.	5.6	2
5	Engineering Relaxation-Paths of C-Exciton for Constructing Band Nesting Bypass in WS₂ Monolayer. Nano Letters, 2022, 22, 3699-3706.	9.1	6
6	Enhanced Photostability and Photoluminescence of PbI 2 via Constructing Typeâ€Ⅰ Heterostructure with ZnO. Advanced Photonics Research, 2021, 2, 2000183.	3.6	2
7	Enhanced Photostability and Photoluminescence of PbI₂ via Constructing Typeâ€Ⅰ Heterostructure with ZnO. Advanced Photonics Research, 2021, 2, 2170017.	3.6	0
8	Revealing the interrelation between C- and A-exciton dynamics in monolayer WS2 via transient absorption spectroscopy. Applied Physics Letters, 2021, 119, .	3.3	10
9	Unraveling the synergetic mechanism of physisorption and chemisorption in laser-irradiated monolayer WS2. Nano Research, 2021, 14, 4274-4280.	10.4	6
10	Highly Photoluminescent Monolayer MoS₂ and WS₂ Achieved via Superacid Assisted Vacancy Reparation and Doping Strategy. Laser and Photonics Reviews, 2021, 15, 2100104.	8.7	11
11	Unveiling Bandgap Evolution and Carrier Redistribution in Multilayer WSe 2 : Enhanced Photon Emission via Heat Engineering. Advanced Optical Materials, 2020, 8, 1901226.	7.3	12
12	Enhanced Carrierâ€“Exciton Interactions in Monolayer MoS2 under Applied Voltages. ACS Applied Materials & Interfaces, 2020, 12, 18870-18876.	8.0	7
13	Improved near-UV electroluminescence of ZnO nanorod array LEDs by coupling with a graphene plasmon layer. Nanophotonics, 2019, 8, 2203-2213.	6.0	10
14	Memristors with organicâ€inorganic halide perovskites. InformaÄnÃ-MateriÃ¡ly, 2019, 1, 183-210.	17.3	111
15	CsPbBr₃â€Quantumâ€Dots/Polystyrene@Silica Hybrid Microsphere Structures with Significantly Improved Stability for White LEDs. Advanced Optical Materials, 2019, 7, 1900546.	7.3	59
16	Slow Cooling of Highâ€Energy C Excitons Is Limited by Intervalleyâ€Transfer in Monolayer MoS 2. Laser and Photonics Reviews, 2019, 13, 1800270.	8.7	22
17	Insertion of Nanoscale AgInSbTe Layer between the Ag Electrode and the CH₃NH₃PbI₃ Electrolyte Layer Enabling Enhanced Multilevel Memory. ACS Applied Nano Materials, 2019, 2, 307-314.	5.0	26
18	Resistive Switching: Cyclingâ€Induced Degradation of Organicâ€“Inorganic Perovskiteâ€Based Resistive Switching Memory (Adv. Mater. Technol. 1/2019). Advanced Materials Technologies, 2019, 4, 1970004.	5.8	3

#	ARTICLE	IF	CITATIONS
19	Cyclingâ€Induced Degradation of Organicâ€“Inorganic Perovskiteâ€Based Resistive Switching Memory. Advanced Materials Technologies, 2019, 4, 1800238.	5.8	47
20	Improved Optical Property and Lasing of ZnO Nanowires by Ar Plasma Treatment. Nanoscale Research Letters, 2019, 14, 312.	5.7	14
21	Complementary Resistive Switching Observed in Graphene Oxide-Based Memory Device. IEEE Electron Device Letters, 2018, 39, 488-491.	3.9	25
22	Color-Tunable ZnO/GaN Heterojunction LEDs Achieved by Coupling with Ag Nanowire Surface Plasmons. ACS Applied Materials & Interfaces, 2018, 10, 15812-15819.	8.0	36
23	Oxidized carbon quantum dotâ€“graphene oxide nanocomposites for improving data retention of resistive switching memory. Journal of Materials Chemistry C, 2018, 6, 2026-2033.	5.5	36
24	Improved switching reliability achieved in HfOx based RRAM with mountain-like surface-graphited carbon layer. Applied Surface Science, 2018, 440, 107-112.	6.1	16
25	Intensity-modulated LED achieved through integrating p-GaN/n-ZnO heterojunction with multilevel RRAM. Applied Physics Letters, 2018, 113, .	3.3	13
26	Flexible Artificial Synapses: Transferable and Flexible Artificial Memristive Synapse Based on WO_x Schottky Junction on Arbitrary Substrates (Adv. Electron. Mater. 12/2018). Advanced Electronic Materials, 2018, 4, 1870056.	5.1	6
27	Transferable and Flexible Artificial Memristive Synapse Based on WO_x Schottky Junction on Arbitrary Substrates. Advanced Electronic Materials, 2018, 4, 1800373.	5.1	58
28	Memory Devices: Photocatalytic Reduction of Graphene Oxide-TiO2 Nanocomposites for Improving Resistive-Switching Memory Behaviors (Small 29/2018). Small, 2018, 14, 1870136.	10.0	4
29	Reversible alternation between bipolar and unipolar resistive switching in Ag/MoS₂/Au structure for multilevel flexible memory. Journal of Materials Chemistry C, 2018, 6, 7195-7200.	5.5	63
30	High-temperature driven inter-valley carrier transfer and significant fluorescence enhancement in multilayer WS₂. Nanoscale Horizons, 2018, 3, 598-605.	8.0	13
31	Photocatalytic Reduction of Graphene Oxideâ€“TiO₂ Nanocomposites for Improving Resistiveâ€Switching Memory Behaviors. Small, 2018, 14, e1801325.	10.0	58
32	Graphite Microislands Prepared for Reliability Improvement of Amorphous Carbon Based Resistive Switching Memory. Physica Status Solidi - Rapid Research Letters, 2018, 12, 1800285.	2.4	12
33	Highly uniform switching of HfO2â^'x based RRAM achieved through Ar plasma treatment for low power and multilevel storage. Applied Surface Science, 2018, 458, 216-221.	6.1	39
34	Interface State-Induced Negative Differential Resistance Observed in Hybrid Perovskite Resistive Switching Memory. ACS Applied Materials & Interfaces, 2018, 10, 21755-21763.	8.0	74
35	Enhancement of Exciton Emission from Multilayer MoS₂ at High Temperatures: Intervalley Transfer versus Interlayer Decoupling. Small, 2017, 13, 1700157.	10.0	19
36	Enhanced near-UV electroluminescence from p-GaN/i-Al₂O₃/n-ZnO heterojunction LEDs by optimizing the insulator thickness and introducing surface plasmons of Ag nanowires. Journal of Materials Chemistry C, 2017, 5, 3288-3295.	5.5	40

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37	Understanding the role of lithium sulfide clusters in lithiumâ€“sulfur batteries. Journal of Materials Chemistry A, 2017, 5, 9293-9298.	10.3	43
38	Sp² clustering-induced improvement of resistive switching uniformity in Cu/amorphous carbon/Pt electrochemical metallization memory. Journal of Materials Chemistry C, 2017, 5, 5420-5425.	5.5	26
39	Significant improvement of near-UV electroluminescence from ZnO quantum dot LEDs via coupling with carbon nanodot surface plasmons. Nanoscale, 2017, 9, 14592-14601.	5.6	38
40	Stable and metallic two-dimensional TaC₂as an anode material for lithium-ion battery. Journal of Materials Chemistry A, 2017, 5, 18698-18706.	10.3	75
41	Controlled Gas Molecules Doping of Monolayer MoS₂ via Atomic-Layer-Deposited Al₂O₃ Films. ACS Applied Materials & Interfaces, 2017, 9, 27402-27408.	8.0	23
42	Enhanced Electroluminescence from ZnO Quantum Dot Lightâ€Emitting Diodes via Introducing Al₂O₃ Retarding Layer and Ag@ZnO Hybrid Nanodots. Advanced Optical Materials, 2017, 5, 1700493.	7.3	21
43	Abnormal high-temperature luminescence enhancement observed in monolayer MoS₂ flakes: thermo-driven transition from negatively charged trions to neutral excitons. Journal of Materials Chemistry C, 2016, 4, 9187-9196.	5.5	15
44	Reliability Improvement of Amorphous Carbon Based Resistive Switching Memory by Inserting Nanoporous Layer. IEEE Electron Device Letters, 2016, 37, 1430-1433.	3.9	21
45	Enhanced Ultraviolet Random Lasing from Au/MgO/ZnO Heterostructure by Introducing p-Cu₂O Hole-Injection Layer. ACS Applied Materials & Interfaces, 2016, 8, 31485-31490.	8.0	13
46	Effect of SiO₂ Spacer-Layer Thickness on Localized Surface Plasmon-Enhanced ZnO Nanorod Array LEDs. ACS Applied Materials & Interfaces, 2016, 8, 1653-1660.	8.0	49
47	Nonvolatile/volatile behaviors and quantized conductance observed in resistive switching memory based on amorphous carbon. Carbon, 2015, 91, 38-44.	10.3	90
48	Recent progress in ZnO-based heterojunction ultraviolet light-emitting devices. Science Bulletin, 2014, 59, 1219-1227.	1.7	10